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Sommario/riassunto

"The book will address fundamentals of THz devices and their applications. THz technology relates to applications that span in frequency from a few hundred GHz to more than 1000 GHz. They require devices for signal generation, detection and treatment the characteristics of which have been reported in various publications but their in-depth understanding is often lacking or requires the consultation of multiple references. It is the purpose of this book to address the above topics in a way that both the beginner and advanced reader can obtain a better understanding of device operation and use"

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